

# Industry's First 800 Mbps DDR2 SDRAMs for High-Performance Memory Modules

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Elpida Memory, Inc. (Elpida), Japan's leading global supplier of Dynamic Random Access Memory (DRAM), today announced the industry's first 256 Megabit DDR2 SDRAM devices that achieve 800 Megabits per second (Mbps) operation. The monolithic devices are available in either x 8- or x 16-bit widths and are intended for use in DDR2 Unbuffered Dual In-line Memory Modules (DIMMs) targeted for the high-end PC market. The devices underwent evaluation and have gained the support of several Taiwanese module manufacturers, A-DATA Technology and Transcend Information Inc.

"As a module maker, we require cutting-edge, high-performance DRAM devices that keep us at ahead of market demand," said Simon Chen, Chairman of A-DATA. "Elpida's 256 Megabit DDR2 800 Mbps devices provide superior performance allowing us to meet the speed demands dictated by our high-end PC customers, especially those in niche markets such as gaming."

"800 Mbps is a major milestone for DDR2 SDRAM," said Jun Kitano, Director of Technical Marketing for Elpida Memory (USA). "It is an ideal match for the latest processor front-side bus, allowing PCs to maximize data throughput at a rate that is faster than ever before possible. Elpida's ability to offer customers advanced DRAM products reinforces our position as industry leader in DRAM development and technology."

"Our customers in the PC market are quickly increasing demand for

high-speed DDR2 SDRAM," said Benjamin Tzou, R&D Manager at Transcend. "As a module manufacturer, we must supply stable, high-performance products and Elpida's devices meet this challenge. Our evaluation of the 800 Mbps devices yielded excellent results in both performance and power consumption, two elements that are crucial in the PC industry."

## **800 Mbps 256 Megabit DDR2 SDRAM - Technical Details**

Elpida's 256 Megabit DDR2 devices (Part numbers: EDE2508ABSE, EDE2516ABSE) are organized as 8M words x 8-bits x 4 banks and 4M words x 16-bits x 4 banks, respectively. They are produced using Elpida's advanced 0.10-micron process technology and are available in 60-ball FBGA (EDE2508ABSE) and 84-ball FBGA (EDE2516ABSE) packages. The devices feature low, 1.85 volt operation with a burst length of 4, 8 and CAS Latency (CL) of 5.

### **Availability**

Elpida's 256 Megabit, x 8-bit DDR2 SDRAM device is (Part number: EDE2508ABSE,) currently sampling to customers. The x 16-bit device (Part number: EDE2516ABSE) samples will be available in early April 2005. Volume production for both devices is expected in May 2005.

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